

P-Channel Power MOSFET

-20V, -11A, 16mΩ

FEATURES

- Improved dV/dt capability
- Fast Switching
- Suitable for 1.8V drive applications
- Pb-free plating
- RoHS compliant
- Halogen-free mold compound

APPLICATION

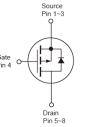
- Load Switch
- Networking

KEY PERFORMANCE PARAMETERS					
PARAN	IETER	VALUE	UNIT		
V _{DS}		-20	V		
R _{DS(on)} (max)	$V_{GS} = -4.5V$	16			
	$V_{GS} = -2.5V$	22	mΩ		
	$V_{GS} = -1.8V$	28			
Qg		27	nC		









Notes: Moisture sensitivity level: level 3. Per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V _{DS}	-20	V		
Gate-Source Voltage		V _{GS}	±10	V		
Continuous Drain Current (Note 1)	T _C = 25°C		-11			
	$T_{c} = 100^{\circ}C$	I _D	-7			
Pulsed Drain Current (Note 2)		I _{DM}	-44	А		
Total Power Dissipation @ $T_c = 25^{\circ}C$		P _{DTOT}	2.5	W		
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C		

THERMAL PERFORMANCE						
PARAMETER SYMBOL LIMIT UNI						
Junction to Case Thermal Resistance	R _{eJC}	25	°C/W			
Junction to Ambient Thermal Resistance	R _{eja}	50	°C/W			

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.

TSM160P02



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PARAMETER	CONDITIONS	TIONS SYMBOL		ТҮР	MAX	UNIT	
Static (Note 3)				1			
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = -250µA BV _{DSS} -20			V			
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	V _{GS(TH)}	-0.3	-0.6	-1.0	V	
Gate Body Leakage	$V_{GS} = \pm 10V, V_{DS} = 0V$	I _{GSS}			±100	nA	
Zero Gate Voltage Drain Current	$V_{DS} = -20V, V_{GS} = 0V$	I _{DSS}			-1	μA	
	$V_{GS} = -4.5V, I_{D} = -6A$			12	16		
Drain-Source On-State Resistance	$V_{GS} = -2.5V, I_D = -4A$	R _{DS(ON)}		16	22	mΩ	
	$V_{GS} = -1.8V, I_{D} = -3A$			21	28	28	
Dynamic ^(Note 4)	·						
Total Gate Charge		Qg		27			
Gate-Source Charge	$V_{DS} = -10V, I_D = -6A,$	Q _{gs}		2.4		nC	
Gate-Drain Charge	$V_{GS} = -4.5V$	Q _{gd}		5.3			
Input Capacitance		C _{iss}		2320			
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$	C _{oss}		280		pF	
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		175			
Switching (Note 5)	·						
Turn-On Delay Time		t _{d(on)}		16.2			
Turn-On Rise Time	$V_{DD} = -10V,$	t _r		43.5			
Turn-Off Delay Time	$R_{GEN} = 25\Omega,$ $I_D = -1A, V_{GS} = -4.5V,$	t _{d(off)}		114		ns	
Turn-Off Fall Time	$10 - 17, v_{\rm GS} = -4.5 v,$	t _f		28.8			
Source-Drain Diode (Note 3)	·				·		
Forward On Voltage	$I_{\rm S} = -1$ A, $V_{\rm GS} = 0$ V	V _{SD}			-1	V	

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

3. Pulse test: PW \leq 300µs, duty cycle \leq 2%

4. For DESIGN AID ONLY, not subject to production testing.

5. Switching time is essentially independent of operating temperature.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM160P02CS RLG	SOP-8	2,500pcs / 13"Reel

Note:

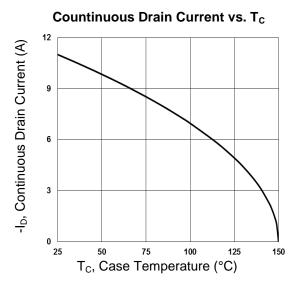
1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC

2. Halogen-free according to IEC 61249-2-21 definition

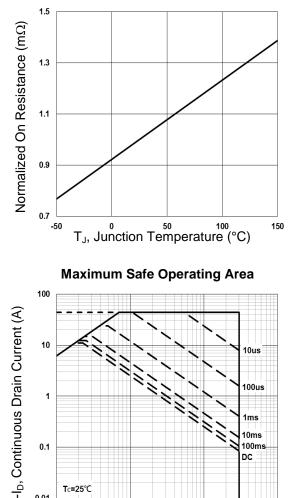


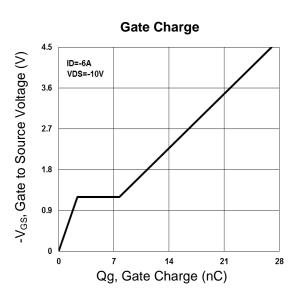
CHARACTERISTICS CURVES

 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$

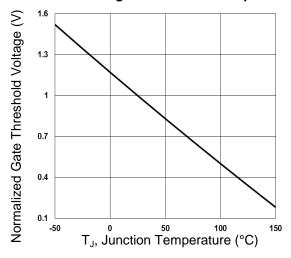


On-Resistance vs. Junction Temperature

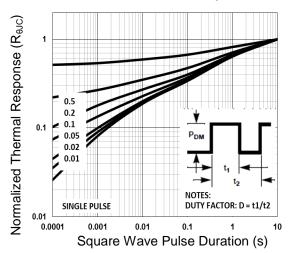




Threshold Voltage vs. Junction Temperature



Normalized Thermal Transient Impedance Curve



Tc=25°C

1

-V_{DS}, Drain to Source Voltage (V)

0.1

0.01

0.1

lms

10ms

100ms DC

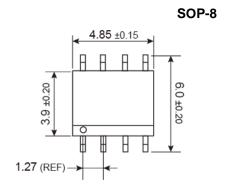
100

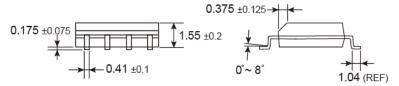
10



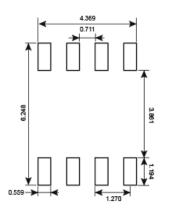


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)





SUGGESTED PAD LAYOUT



=Apr

MARKING DIAGRAM

′ = Year Co	Y		
I = Month C	М		
O =J			160PC
S =N		95	YML
W =S		ΠП	
= Lot Code	L		#1U U

= Year	Code					
= Mont	th Code	for I	Haloger	n Fre	e Produ	ct
0	=Jan	Ρ	=Feb	Q	=Mar	R
_		_				

S	=May	Т	=Jun	U	=Jul	V	=Aug
W	=Sep	Х	=Oct	Y	=Nov	Ζ	=Dec
= Lot C	Code (1~	-9, A	∧~Z)				



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